

# Application Manual

## Real Time Clock Module

## **RTC-9701JE**

Model	Product Number
RTC-9701JE	Q4197017x000100



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#### **Serial RTC Module with Alarm and Timer Function**

## RTC - 9701JE

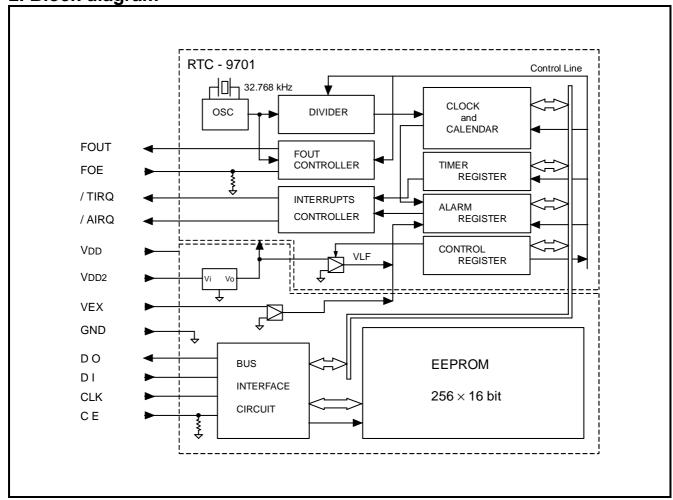
- Built-in 32.768 kHz crystal oscillator with frequency adjusted
- Alarm interrupt function for day of the week, day, hour, and minute
- Interval timer interrupt function
- Voltage decrease alarm function
- Time update alarm function
- · Automatic adjustment for leap year
- Voltage detection function
- Nonvolatile 4 kbit (256×16 bit) memory
- Main power supply (VDD)  $2.7 \text{ V} \sim 3.6 \text{ V}$
- Backup power supply (VDD2) 1.8 V  $\sim$  5.5 V Low current consumption at 0.8  $\mu A$  / 3 V (Typ.)
- Available as small package (JE: VSOJ-20 pin)

### 1. Overview

This module is a high precision RTC module with serial interface in 4 lines form (or 3 lines form). It has a built-in 32.768 kHz crystal oscillator.

The system IC in the package has a variety of built-in functions such as high precision clock circuitry, crystal oscillator, 32.768 kHz output, nonvolatile memory, voltage detection circuitry, alarm and timer.

2. Block diagram



## 3. Terminal description

## 3.1. Terminal connections

erri reminare cominectiv								
		RTC - 9701 J	E					
1.	V <sub>DD2</sub>			20.	N.C.			
2.	VEX	# 1	#20	19.	N.C.			
3.	FOE		1	18.	N.C.			
4.	/AIRQ	4		17.	N.C.			
5.	/TIRQ		] ]	16.	N.C.			
6.	CE		D D	15.	N.C.			
7.	CLK		]	14.	N.C.			
8.	DI		Í	13.	GND			
9.	DO	#10	#11	12.	GND			
10.	V <sub>D</sub> D			11.	FOUT			
	VSOJ - 20 pin							

### 3.2.Pin functions

Pin name	Pin number	1/O**1	Functions
VDD2	1	_	RTC power (backup power). This pin is connected to the plus side of the power. (Always supply the power irrespective of action situation to this terminal.)
VEX *2	2	Input	External voltage detection input pin. If external voltage decreases blow VEX,EXF bit became "1".  Note: This function acts only when VDD2 is supplied the power.
FOE	3	Input	This is an input pin to control FOUT output.  When the FOE pin is at the "H" level, the FOUT pin goes into the output state; when it is at the "L" level, the FOUT pin becomes Low.
/AIRQ	4	Input	This is the open drain output pin for alarm and time update interrupts.
/TIRQ	5	Output	This is the open drain output pin for timer interrupt.
CE	6	Input	This is a chip enabled input pin with the built-in pull-down resistor.  When the CE pin is at the "H" level, access to this RTC becomes possible.  When the CE pin is at the "L" level, the DO pin is at the high impedance level, and the CLK and DI pins would not accept input.
CLK	7	Output	This is the shift clock input pin for serial data transfer.  In the write mode, it takes in data from the DI pin using the CLK signal rise edge. In the read mode, it outputs data from the DO pin using the fall edge.
DI	8	Output	Serial data input pin
DO	9	Input	Serial data output pin
VDD *2	10	Output	Main power. This pin is connected to the plus side of the power.
FOUT	11	_	This pin outputs the reference clock signal at 32.768 kHz (CMOS output). Depending on the level of the FOE input pin, output from the FOUT pin can be prohibited.
GND			This pin is connected to the minus side (ground) of the power.
N.C.	14 – 22	_	This pin is not connected to the IC chip. All the N.C. pins are connected collectively with the inside frame.  Connect this pin to OPEN, GND, or VDD.

<sup>\*1 )</sup> I: CMOS INPUT, O: CMOS OUTPUT, AIN: Analog INPUT, O.D.: Open Drain Output

 $<sup>^{\</sup>star 2}$  ) Be sure to connect a filter capacitor of at least 0.1  $\mu\text{F}$  near VDD–GND, VDD2–GND and VEX–GND.

4. Absolute maximum ratings

GND=0 V

Item	Symbol	Condition	Rating	Unit
Power voltage	Vdd, Vdd2	Vdd-GND, Vdd2-GND	-0.3 to +6.0	V
Input voltage	VIN	Input pin	GND-0.3 to VDD+0.3	V
	VAIN	VEX pin	GND-0.3 to +6.0	
Output voltage	Vout	/AIRQ, /TIRQ, FOUT, DO pins	GND-0.3 to VDD+0.3	V
Storage temperature	Tstg	Stored bare product after unpacking	–55 to +125	°C

5. Recommended operating conditions

GND=0 V

Item	Symbol	Condition	Rating	Unit
Operating power voltage	Vdd	VDD pin	2.7 to 3.6	V
RTC power voltage	VDD2	Vdd2 pin	1.8 to 5.5	V
Analog power voltage	VEX	VEX pin	1.4 to 5.5	V
Operating temperature	Topr	No condensation	-40 to +85	°C

6. Frequency characteristics

GND=0 V

Item	Symbol	Condition	Rating	Unit
Frequency accuracy / Clock accuracy	Δf/fo	Ta= +25 °C VDD2=3.0 V 5 ± 23 <sup>(*1)</sup>		× 10 <sup>-6</sup>
Frequency voltage characteristics	f/V	Ta= +25 °C VDD=1.8 V to 5.5 V	± 2 Max.	imes 10 <sup>-6</sup> / V
Frequency temperature characteristics	Тор	Ta= -10 °C to +70 °C VDD= 3.0 V; reference at +25 °C	+10 / –120	× 10 <sup>-6</sup>
Oscillation start up time	tsta	Ta= +25 °C VDD=3.0 V	3 Max.	s
Aging	fa	Ta= +25 °C VDD=3.0 V ; first year	± 5 Max.	× 10 <sup>-6</sup> / year

<sup>\*1)</sup> Equivalent to 1 minute of monthly deviation (excluding offset).

## 7. DC Electrical characteristics

\*If not specifically indicated, VDD=2.7 V to 3.6 V, VDD2=1.8 V to 5.5 V, GND=0 V, Ta= -40 °C to +85 °C

Item	Symbol	Conditi	on	Min.	Тур.	Max.	Unit
VDD current	IDD1	VDD=3.0 V, FOUT; output OFF			0.2	3.0	^
consumption	IDD2	VDD=3.0 V, CL=0 pF, FOUT; 32.768 kHz output	: ON		1.0	3.5	μΑ
VDD2 current	IBK1	VDD2=3.0 V, FOUT; output OFF			0.8	1.0	
consumption	Івк2	VDD2=3.0 V, CL=0 pF, FOUT; 32.768 kHz output	: ON		0.8	1.0	μΑ
"H" input voltage	ViH	CE, CLK, DI, FOE pin	0.8VDD		VDD	V	
"L" input voltage	VIL	CE, CLK, DI, FOE pin		0		0.2Vdd	V
"H" Output	Voh1	FOUT pin	IOH = −1 mA	VDD-0.4		Vdd	V
voltage	VOH2	DO pin	IOH = −1 mA	VDD-0.4		Vdd	v
"L" Output	VOL1	FOUT pin	IOL = 1 mA	GND		GND+0.4	
voltage	VOL2	DO pin	IOL = 1 mA	GND		GND+0.4	V
voltage	VOL3	/AIRQ, /TIRQ pin	IoL = 2 mA	GND		GND+0.4	
Input resistor	RDWN	CE, FOE pin	VIN = VDD or GND	75		600	kΩ
Input leakage current	ILK	CE, CLK, DI, FOE pin	Vout = Vdd or GND	-0.5		0.5	μΑ
Output leakage current	loz	DO, /AIRQ, /TIRQ, FOUT pin	VIN = VDD or GND	-0.5		0.5	μΑ

## 8. AC Electrical characteristics

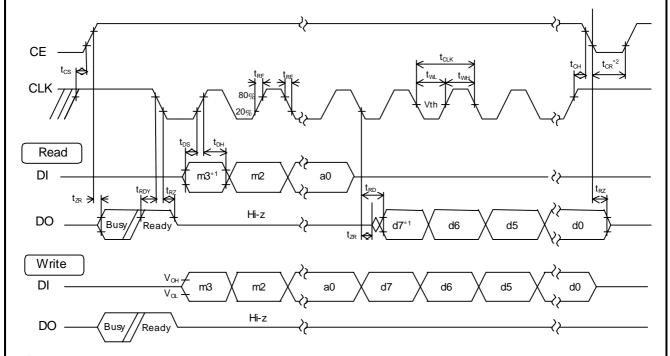
\*If not specifically indicated, VDD=2.7 V to 3.6 V, VDD2=1.8 V to 5.5 V, GND=0 V, Ta= -40 °C to +85 °C

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
CLK clock cycle	tclk	Vth = 50% VDD	500			ns
CLK H pulse width	twH	Vth = 50% VDD	230			ns
CLK L pulse width	twL	Vth = 50% VDD	230			ns
CE setup time	tcs		110			ns
CE hold time	tcH		170			ns
Write data setup time	tDS		150			ns
Write data hold time	tDH		150			ns
Read data delay time	trd	$C_L = 65 \text{ pF} \pm 10 \text{ pF}$			240	ns
DO output switching time	tzr	$C_L = 65 \text{ pF} \pm 10 \text{ pF}$	170			ns
DO output disable time	trz	CL = 65 pF ± 10 pF RL = 10 k			240	ns
Ready setup time	trdy		65			ns
CLK rise and fall time	trf	20 % ~ 80 % of VDD			30	ns
Carry Busy *1	tcarry	X'tal = 32.768 kHz			7.8125	ms
FOUT Duty	tw / t	Vth = 50% VDD VDD = 3.0V	40	50	60	%

<sup>\*1)</sup> Since "writing to EEPROM: twnv" and "performing carry action: tcarry" are OR output, maximum of 17.8125ms Busy signal output.

#### Read & Write Timing

With exception of data transfer at initial power supply and at voltage decrease of VDD2, hold the carry operation when transfering data, so that the DO pin will output the Busy signal (0:Busy / 1:Ready) right after communication starts (CE=HIGH). If it's at the Ready state, communication is permitted. If it's at the Busy state, either the clock is being updated or the EEPROM Memory is being written. In this case, wait until it becomes Ready, or stop communication (CE=LOW) once to restart some time after. By any chance a data is transferred when it is at the Busy state, that data is not guranteed to be safe. The Busy signal becomes Hi-z at the timing when the initial rise edge of the clock occurs.



- \*1) The address width and the data width in the RTC mode differs for those in the EEPROM Memory mode.
- \*2) If the Busy/Ready signal is ignored, make sure to reserve 16 ms at least once every second.
- \*3) Latch data at the positive edge. (Data is output at the Negative Edge of clock signal.)
- \*4 ) Since the registers are undefined at initial power supply as well as after voltage decrease of VDD2, the Ready signal may not output. After power supply, reserve more than 20ms, and then check the Busy / Ready signal. If the Ready signal is not output in more than 17.8125 ms, access by ignoring the Busy signal and initialize all the registers.

## 9. Voltage detection characteristics

\*If not specifically indicated, VDD=2.7 V to 3.6 V, VDD2=1.8 V to 5.5 V,GND=0 V, Ta= -40 °C to +85 °C

9.1. VEX voltage detection characteristics

Item	Signal	Condition	Min.	Тур.	Max.	Unit
Current consumption	IDDVEX	VEX = 3.0 V	10	20	40	μΑ
Operation voltage for detection circuitry	VEX	VEX pin	2.3	2.5	2.7	V
Hysteresis voltage	VHYS		70	120	170	mV
Low active voltage	VACT	IOL = 1  mA, $VOL = 0.4  V$	1.4			V

<sup>\*</sup> Be sure to connect a filter capacitor of at least 0.1 μF near VEX-GND.

### 9.2. VLF voltage detection characteristics

circuitry

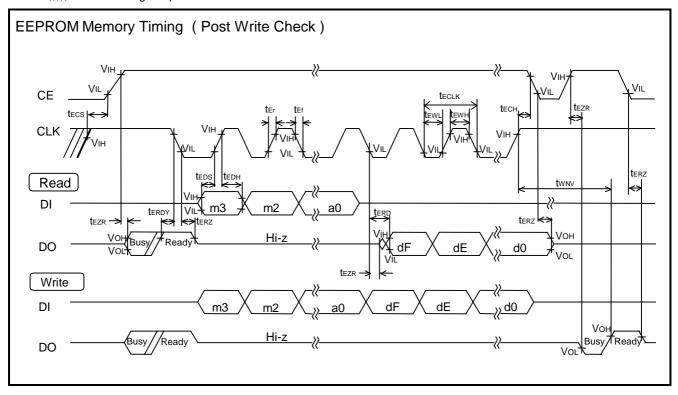
\*If not specifically indicated, VDD=2.7 V to 3.6 V, VDD2=1.8 V to 5.5 V,GND=0 V, Ta= -40 °C to +85 °C

Item	Signal	Condition	Min.	Тур.	Max.	Unit
Current consumption	IDDVLF	VLF constant enable	3	10	30	μΑ
Operation voltage for detection	VLF	V <sub>DD2</sub> pin	1.4	1.8	2.2	V

## **10. EEPROM Memory characteristics** \* If not specifically indicated,GND=0 V, VDD=2.7 V to 3.6 V, VDD2=1.8 V to 5.5 V, Ta=-40 °C to +85 °C

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Memory configuration			4 kb	it ( 256 × 16	bit)	_
Program/Erase cycle			10 <sup>5</sup>			times
Current consumption	IDD3	Write to EEPROM		1	3	mA
Access time	twnv			5	10	ms
CLK clock cycle	troux	$VDD = 3.0 V \pm 0.3 V$	1000			ns
CEN CIOCK CYCIE	tECLK	$VDD = 3.3 V \pm 0.3 V$	900			ns
CLK H pulse width	tewn		430			ns
CLK L pulse width	tewL		430			ns
CE setup time	t <sub>ECS</sub>		110			ns
CE hold time	tECH		150			ns
Write data setup time	t <sub>EDS</sub>		150			ns
Write data hold time	t <sub>EDH</sub>		160			ns
Read data delay time	t <sub>ERD</sub>	$CL = 65 pF \pm 10 pF$			240	ns
DO output switching time	tezr	$C_L = 65 \text{ pF} \pm 10 \text{ pF}$	170			ns
DO output disable time	t <sub>ERZ</sub>	CL = 65 pF ± 10 pF RL = 10 k			240	ns
Ready setup time	terdy		65			ns
Input rise and fall time	t <sub>Er,tEf</sub>	20 % to 80 % of VDD			30	ns

<sup>\*</sup> Power for the EEPROM Memory is supplied from VDD. In order to turn the power OFF after writing, make sure to save  $t_{WNV}$  before turning the power OFF.



## 11. Register table

### 11.1. Register table

11.1.1. RTC register table (when the RTC mode is set)

Add ress	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	R/W	Comments
0	SEC	*1	S40	S20	S10	S8	S4	S2	S1	R/W	BCD notation
1	MIN	0	M40	M20	M10	M8	M4	M2	M1	R/W	BCD notation
2	HOUR	0	0	H20	H10	H8	H4	H2	H1	R/W	BCD notation
3	WEEK	0	W6	W5	W4	W3	W2	W1	W0	R/W	2 <sup>n</sup> notation
4	DAY	0	0	D20	D10	D8	D4	D2	D1	R/W	BCD notation
5	MONTH	0	0	0	C10	C8	C4	C2	C1	R/W	BCD notation
6	YEAR	Y80	Y40	Y20	Y10	Y8	Y4	Y2	Y1	R/W	BCD notation
7	*2 Y100	0	0	1	0	0	0	0	0	R	20 is fixed (BCD)
8	MIN Alarm	AE	MA40	MA20	MA10	MA8	MA4	MA2	MA1	R/W	BCD notation
9	HOUR Alarm	AE	0	HA20	HA10	HA8	HA4	HA2	HA1	R/W	BCD notation
Α	WEEK Alarm	AE	WA6	WA5	WA4	WA3	WA2	WA1	WA0	R/W	WADA=0
Α	DAY Alarm	AL.	0	DA20	DA10	DA8	DA4	DA2	DA1	-	WADA=1
В	*3 Reserved				Rese	erved				R/W Prohibition	R/W Prohibition
С	Interval Timer	TDUTY	CT6	CT5	CT4	СТЗ	CT2	CT1	CT0	R/W	_
D	Extension Reg.	TEST *4	WADA	UDUTY	USEL	0	0	TSEL1	TSEL0	R/W	_
Е	*5 Flag Reg.	VLF2	0	UF	TF	AF	EXF	VLF	0	R/W	_
F	Control Reg.	0	0	UIE	TIE	AIE	EXIE	VLIE	0	R/W	-

- Note1. 1. At the initial power supply, the values of the registers are not fixed, so please initialize them before use. While initializing, do not set impossible data for date and time; otherwise there is no guarantee that the clock will operate properly.
- Note2. \*1."0" is read where "o" is marked. When writing data, use "0".
  - \*2. Since these are read-only bits, write is not permitted.
  - \*3. The Resreved register used by EPSON for testing. Setting does not do.
  - \*4. The TEST bit is used by EPSON for testing. Be sure to set it to "0" before use.
  - \*5. The flag bit will cleared with "0". ( "0" can not be replace to "1".)

#### 11.1.2. EEPROM Memory table (When EEPROM Memory mode is set.)

Sogmont	Segment Address Data												Comments					
Segment	Address	dF	dE	dD	dC	dB	dA	d9	d8	d7	d6	d5	d4	d3	d2	d1	d0	Comments
0	00																	
	:		User Memory												4 kbit ( 256 × 16 bit )			
	FF																	

#### 11.2. Description of RTC functions (addresses between 0 and 7)

The clock and the caledar consists of seconds, minutes, hours, day of the week, day, month, year and every 100 year (SEC, MIN, HOUR, WEEK, DAY, MONTH, YEAR and Y100 registers).

bit 7 R/W Address Function bit 6 bit 5 bit 4 bit 3 bit 2 bit 1 bit 0 Comments S8 S40 S20 S10 S4 BCD notation SEC 0 S<sub>2</sub> S1 R/W MIN 0 M40 M20 M10 **M8 M4** M2 M1 R/W BCD notation 1 2 HOUR 0 0 H20 H10 H8 H4 H2 H1 R/W BCD notation W5 **WEEK** 0 W6 W4 W3 W2 W1 W0 R/W 3 D8 D1 4 DAY 0 0 D20 D10 D4 D2 R/W BCD notation MONTH 0 0 C8 C4 C2 C1 R/W BCD notation 5 C10 0 Y80 Y40 Y20 <u>Y4</u> 6 YEAR Y10 **Y8** Y2 Υ1 R/W BCD notation 7 Y100 0 0 0 0 0 0 0 R 20 is fixed (BCD) 1

#### 11.2.1. SEC register and MIN register (addresses 0 and 1)

These registers are 60-base BCD counters.

These registers are incremented at the timing when carry is generated from a lower register. At the timing when the lower register changes from 59 to 60, carry is generated to the higher register and thus incremented. (If inappropriate value (like 65) is set, the SEC/MIN register is cleared to "0" (at the incrementation) and carry may be generated to the higher register.) When data is written to the MIN register, all the counters lower than it are cleared. Clearing occurs right after CLK data latch

#### 11.2.2. HOUR register (address 2)

of D0 data.

This register is a 24-base BCD counter (24 hour format).

This register is incremented at the timing when carry is generated from the MIN register. At the timing when this register changes from 23 to 00, carry is generated to the WEEK register and the DAY register.

		24h format											
a.m.	00	01	02	03	04	05	06	07	08	09	10	11	
p.m.	12	13	14	15	16	17	18	19	20	21	22	23	

#### 11.2.3. WEEK register (address 3)

This register is a septenary BCD counter (counts from 0 to 6). It is incremented when carry is generated from the HOUR register. This register does not generate carry to a higher register. Since this register is not connected with the YEAR, MONTH and DAY registers, it needs to be set again with the matching day of the week if any of the YEAR, MONTH or DAY registers have been changed. As in the WEEK alarm register, this register is in 2<sup>n</sup> format.

Day of the week	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
		W6	W5	W4	W3	W2	W1	W0
Sunday	0	0	0	0	0	0	0	1
Monday	0	0	0	0	0	0	1	0
Tuesday	0	0	0	0	0	1	0	0
Wednesday	0	0	0	0	1	0	0	0
Thursday	0	0	0	1	0	0	0	0
Friday	0	0	1	0	0	0	0	0
Saturday	0	1	0	0	0	0	0	0

<sup>\*</sup> Be careful not to write "1" to multiple bits.

#### 11.2.4. DAY register and MONTH register (addresses 4 and 5)

The DAY register is a variable (between 28-base and 31-base) BCD counter that is influenced by the month and the leap year. It is incremented when carry is generated from the lower register. (If inappropriate values are set for day and month, the DAY register is set to 01 (at incrementation) and carry may be generated to the higher register.)

DAY register: 01 to 28, 29, 30, or 31 (depending on the month and the leap year)

MONTH register: 01 to 12

			.0.0 0	<u> </u>									
		Jan.	Feb.	Marc h	April	May	June	July	Aug.	Sep.	Oct.	Nov.	Dec.
Last day	Normal year Leap year	31	28 29	31	30	31	30	31	31	30	31	30	31

#### 11.2.5. YEAR register (address 6 and 7)

This register is a BCD counter for years 2000 to 2099. The YEAR register is extended to display the year directly. Also, the leap year is automatically determined, which reflects in the DAY register.

Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	R/W	Comments
6	YEAR	Y80	Y40	Y20	Y10	Y8	Y4	Y2	Y1	R/W	BCD notation
7	Y100	0	0	1	0	0	0	0	0	R	20 is fixed (BCD)

<sup>\*</sup> Leap year is a year that can be divided by four (multiples of 100 is excluded except multiples of 400).

#### 11.3. Alarm functions (/AIRQ)

From the conditions of the event flags (AF, EXF, VLF and VLF2), you can know the conditions when the clock matches, when the voltage decreases and when the oscillation stops. The data of these bits are kept until cleared with "0". Also, since output to /AIRQ is possible when each event (except VLF2) is generated, interrupt can be requested to the host.

#### 11.3.1. Time alarm (addresses between 8 and A)

#### 11.3.1.1. Explanation of Time alarm (1).

When the registers corresponding to the minute, the hour, and the day of the week matches with the clock (comparing it right after carry is generated 7.8125 ms later), the alarm matching flag (AF) becomes "1". At this moment, if the AIE (Alarm Interrupt Enable) is enabled ("1"), the /AIRQ pin outputs Active Low.

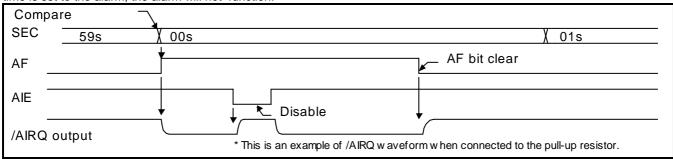
With the AE bit (bit 7: the Alarm Enable Don't care bit) of each alarm registers, the HOUR alarm and the DAY alarm can be set. For the day of the WEEK alarm, multiple days can be set (i.e. Saturdays and Sundays). The WADA bit specifies the alarm to use between the WEEK alarm and the DAY alarm.

Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	R/W	Comments
8	MIN alarm	AE	MA40	MA20	MA10	MA8	MA4	MA2	MA1	R/W	BCD notation
9	HOUR alarm	AE	0	HA20	HA10	HA8	HA4	HA2	HA1	R/W	BCD notation
Α	WEEK alarm	ΑE	WA6	WA5	WA4	WA3	WA2	WA1	WA0	R/W	WADA=0
	DAY alarm		0	DA20	DA10	DA8	DA4	DA2	DA1		WADA=1
D	Extension reg.		WADA							R/W	
Е	Flag reg.					AF				R/W	
F	Control reg.					AIE				R/W	

Bit name	Bit data	Function	Comments
AE	0	Compares the corresponding register	This is in negative logic, so be careful.
	1	Does not compare the corresponding register (don't care)	
AIE	0	/AIRQ output is prohibited	
	1	/AIRQ output (alarm interrupt is valid)	
AF	0	Alarm unmatched	-
	1	Alarm matched	This bit is kept until overwriting with "0".
WADA	0	WEEK alarm is set	
	1	DAY alarm is set	

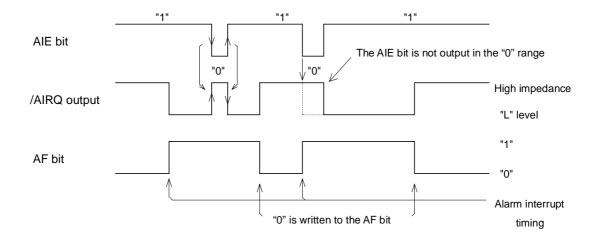
To avoid malfunction, the compare operation is halted while writing to the alarm registers. If write to the alarm register during this time (period of 7.58ms from carry occurrence), the alarm will not function.

The compare operation is performed during the carry operation (the interval of the lowest carry digit of the AE enabled register). If the AF bit is cleared exactly when the time matches the alarm data, the alarm will not function. Even if the current time is set to the alarm, the alarm will not function.



#### 11.3.1.2. Explanation of Time alarm (2).

When the alarm matches and AIE=1, the /AIRQ pin outputs "L"; when AIE=0, the /AIRQ pin is at the high impedance level.



#### 1) How to use

The day of the week, day, hours and minutes can be set. For the day of the week, multiple days can be set at one time. The WADA bit specifies which alarm is used between the WEEK alarm and the DAY alarm.

To avoid unintended hardware interrupt during the alarm setup, it is recommended that AIE bit be initially set to "0". Then, set up the alarm data, and apply zero clear to the AF flag in order to initialize (with certainty) the alarm circuitry. Afterward, set the AIE bit to "1". If you desire no hardware interrupt, set the AIE bit to "0", and monitor the AF bit with software as required.

#### 2) Usage example

- a) Set the alarm to go off at 6 p.m. tomorrow (when the WADA bit specifies the WEEK alarm).
  - Write "0" to the AIE bit and "0" to the AF bit.
  - Write "0" to the WADA bit (selects the WEEK alarm).
    Write "1" to the AE bit of the WEEK/DAY alarm.

  - Shift the current day of the week recorded in the WEEK alarm register 1 bit to the left, then write this data to the WEEK alarm register.
    - (If bit 6 is set to "1" (Saturday), then write "01h" (Sunday).)
  - Write "18h" to the HOUR alarm register.Write "00h" to the MIN alarm register.

  - Clear the AF bit to zero.
  - Write "1" to the AIE bit.
- b) Set the alarm to go off at 6 a.m. every morning except Saturdays and Sundays.
  - Write "0" to the AIE bit and "0" to the AF bit.
  - Write "0" to the WADA bit (selects the WEEK alarm).
  - Write "3Eh" to the WEEK alarm register.
  - Write "06h" to the HOUR alarm register.
  - Write "00h" to the MIN alarm register.
  - Clear the AF bit to zero.
  - Write "1" to the AIE bit.

RTC - 9701 JE EPSON

#### 11.3.2. Voltage detection function

#### 11.3.2.1. VEX voltage decrease alarm (EXF)

With the voltage detection circuitry that is independent from the other power supplies, the VEX voltage can be monitored constantly. If the voltage decreases below VEX, EXF (VDD Low alarm Flag) becomes "1" and /AIRQ (Interrupt Request) becomes Active Low. Even if the voltage recovers, this state is kept until EXF is cleared. Although this circuitry can constantly monitor the voltage in high precision, current is consumed, so be careful.

As chief usage, use it to monitor the voltage of the main battery (for the main power source).

Bit name	Bit data	Function	Comments
EXIE	0	VEX voltage monitor circuitry OFF	
LXIL	1	VEX voltage monitor circuitry ON (constantly)	
EXI	F	Read "1": voltage is below VEX voltage	Kept until overwriting with "0"

#### 11.3.2.2. VDD2 voltage decrease alarm (VLF)

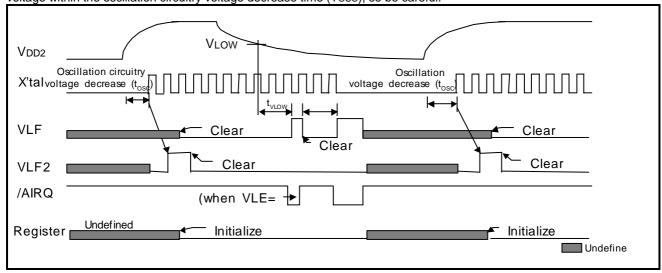
When the VLIE bit is enabled, the VDD2 voltage is monitored once every 10 seconds. During this time, if the voltage decreases below VLOW, VLF (VDD2 Low alarm Flag) becomes "1" and /AIRQ (Interrupt Request) becomes Active Low. This state is kept until VLF is cleared. In this circuitry, if the VLIE bit is disabled, the current consumption may be suppressed to minimum, but the voltage monitor circuitry will not operate.

If the voltage decreases momenterally for less than 10 seconds, VLF may not be detected, so be careful.

Bit name	Bit data	Function	Comments
	0	/AIRQ output is prohibited	V <sub>DD2</sub> voltage monitor circuitry OFF
VLIE	1	/AIRQ output	V <sub>DD2</sub> voltage monitor circuitry ON
	ı		(once every 10 seconds)
VLF	=	Read "1": VDD2 voltage is below VLOW voltage	Kept until overwriting with "0"

#### 11.3.2.3. Oscillation circuitry voltage decrease flag (VLF2)

This is a function to detect decrease in oscillation circuitry voltage. If there had been a previous decrease in oscillation circuitry, VLF2 becomes "1". (/AIRQ will not operate with VLF2 function.) When VLF2 is "1", all the registers except the EEPROM Memory are undefined, so please perform the initial setup. Also, VLF may not detect instantaneous decrease in voltage within the oscillation circuitry voltage decrease time (Tosc), so be careful.

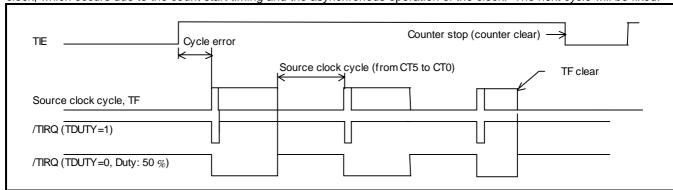


#### 11.4. Timer function (/TIRQ)

#### 11.4.1. Variable interval timer

The interval period and Duty can be set for this interval timer. /TIRQ becomes "0" when TF is released or when the Duty period is expired. The data in TF is kept until it is cleared.

By setting Duty to ON, the current consumption of the pull-up resistor is minimized and intermittent operations on standby are trigger locked; such multipurpose usages become possible. Be careful with the cycle error at the initial cycle of the source clock, which occurs due to the count start timing and the asynchronous operation of the clock. The next cycle will be fixed.



Addr	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	R/W	Comments
С	Interval timer	TDUTY	CT6	CT5	CT4	CT3	CT2	CT1	CT0	R/W	
D	Extension reg.							TSEL1	TSEL0	R/W	
Е	Flag reg.				TF					R/W	
F	Control reg.				TIE					R/W	

	Bit name			Functi	on		Comments
	TIE		0:/TIRQ out 1: /TIRQ ou	tput prohibited It (alarm interrupt is	valid)		
	TF		0:/TIRQ=Hi 1: /TIRQ=A			Opposite logic of /TIRQ	
	TSEL1	TSEL0	Clock	Min.(CT=00 hex)			
	0	0	1024 Hz	0.98	Do not set Duty		
Source	0	1	64 Hz	15.625	2000	ms	
clock	1	0	1 Hz	1	120	S	TDUTY=0
settings	1	1	1 min	1	120	min	(Duty =50 %)
	1	0	2 Hz	0.5	60	S	TDUTY=1 (Low width: 7.8125 ms)
	1	1	1 min	1	120	min	TDUTY=1 (Low width: 3.90625 ms)

#### 11.4.2. Time update interrupt

Generates timer interrupt (/TIRQ) after time update of seconds or minutes. /TIRQ is released when UF is released or when Duty period is expired. The data in UF is kept until it is cleared.

By setting UDUTY to ON, the current consumption of the pull-up resistor is minimized

Addr	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	R/W	Comments
D	Extension reg.			UDUTY	USEL					R/W	
Е	Flag reg.			UF	TF					R/W	
F	Control reg.			UIE	TIE					R/W	

Bit name	Bit data	Function	Comments
UIE	0	/TIRQ output is prohibited	-
OIL	1	/TIRQ output	Default value
UF 0		-	-
OP-	1	Clock update occurred	-
USEL 0		1s interrupt (at 1s carry)	-
USLL	1	1min interrupt (at 00s)	Default value
UDUTY	0	50 % DUTY	-
00011	1	7.8125 ms or 3.90625 ms (low width)	Default value

#### 11.5. Control register / Flag register

Address	Function	bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0	R/W	Comments
D	Extension reg.	TEST	WADA	UDUTY	USEL	0	0	TSEL1	TSEL0	R/W	
Е	Flag reg.	VLF2	0	UF	TF	AF	EXF	VLF	0	R/W	
F	Control reg.	0	0	UIE	TIE	AIE	EXIE	VLIE	0	R/W	

#### 11.5.1. Control register

TEST

This bit is used by EPSON for testing. Be sure to set it to "0".

WADA

This bit sets either the WEEK alarm or the DAY alarm. For details, see the **Time alarm** section [11.3.1.].

• UDUTY, USEL, UIE

This is the time update interrupt bit. For details, see the **Time update interrupt** section [11.4.2.].

TSEL

This is the source clock setting bit for the timer. For details, see the Variable interval timer section [11.4.1.].

EXIE

This is the enable bit for the VEX voltage decrease detection circuitry. For details, see the **VEX voltage decrease alarm** section [11.3.2.1.].

VLIE

This is the enable bit for the VDD2 voltage decrease detection circuitry. For details, see the **VDD2 voltage decrease alarm** section [11.3.2.2.].

• TIE

This is the enable bit for the timer. For details, see the Variable interval timer section [11.4.1.].

AIE

This is the enable bit for the time alarm. For details, see the **Time alarm** section [11.3.1.].

#### 11.5.2. Flag register

This register is the flag register. For each event (alarm and interval timer) generated, "1" is set. Set it to "0" to clear. To keep the corresponding register state, set it to "1" (mask).

• VLF2

This bit is the flag that records oscillation circuitry voltage decrease. For details, see the **Oscillation circuitry voltage** decrease flag (VLF2) section [11.3.2.3.].

• UF

This bit becomes "1" when time update occurs. For details, see the **Time update interrupt** section [11.4.2.].

• TF

During the interval timer, this bit is set to "1" at the Negative Edge of the /TIRQ. For details, see the **Variable interval timer** section [11.4.1.].

EXF

This bit becomes "1" when VEX voltage decrease occurs. For details, see the **VEX voltage decrease alarm** section [11.3.2.1.].

VLF

This bit becomes "1" when VDD2 voltage decrease occurs. For details, see the VDD2 voltage decrease alarm section [11.3.2.2.].

AF

This bit becomes "1" when time match alarm occurs. For details, see the **Time alarm** section [11.3.1.].

## 12. Read / Write data

#### 12.1. Serial data transfer method

This is a serial data transfer method in 4 lines form (or 3 lines form). Mode, address and data are transferred in MSB-first in respective order.

The first 4 bits (called mode field) determines the mode and the data size of the other fields (address and data fields).

### 12.1.1. Mode field

• The first 4 bits determines the mode.

Mode field		m3	m2	m1 m0		
		Read/Write	Reserved	BANK r	egister	
Data bit	0 0 : write		0 *	00: RTC mode 01: Reserved		
Data bit	1	1 : read	0 *	10: EEPROM Memory 11: Reserved		

<sup>\*</sup> Make sure m2 is set to "0".

#### 12.1.2. Address field and data field

#### • RTC mode (m1 bit =0)

Mode field	m3	}	m2	m1	m0				
Address field	a3		a2	a1	a0				
Data field	d7		d6	d5	d4	d3	d2	d1	d0

#### • EEPROM Memory mode (m1 bit =1)

Mode field	m3	m2	m1	m0				
Address field	seg3	seg2	seg1	a7				
	a6	a5	a4	a3	a2	a1	a0	0
Data field	dF	dE	dD	dC	dB	dA	d9	d8
	d7	d6	d5	d4	d3	d2	d1	d0

<sup>\*</sup> Since segment bits (seg3 to seg1) are used for memory expansion, write "0" to them.

#### 12.2. Reading/Writing in RTC mode.

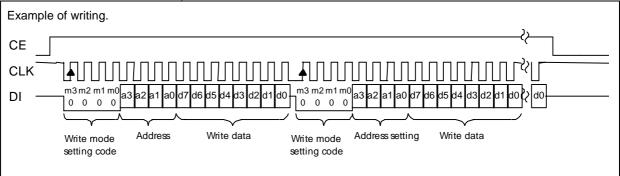
For both reading and writing, after CE input rises, set the 4-bits mode, then specify the 4-bits address, and finally read or write in 8-bits units.

If the input of data in 8-bits unit is not completed before CE input falls, the 8-bits data will be ignored at the time CE input falls (the data before this is undefined).

Reading and writing both uses MSB-first.

#### 12.2.1. Writing in RTC mode. (Cycle mode)

- 1) After CE input rises, set the first 4 bits (write mode setting code) to "1", then write the address in the next 4 bits. Data is written in the following 8 bits.
- 2) The cycle mode can be used only when the RTC mode is set. Since read/write of data can be done continuously, this mode is useful to read the clock data and to overwrite (read/write) the flags (continuous access is limited to 1 second).

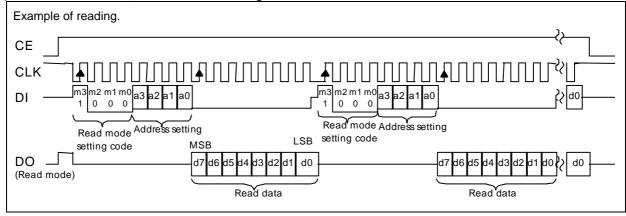


<sup>\*</sup> While transferring data, switching to the EEPROM Memory mode is prohibited.

#### 12.2.2. Reading in RTC mode.

1) After CE input rises, set the first 4 bits (read mode setting code) to "8", then write the address data in the next 4 bits.

2) Read the address data, then read the following 8 bits.



#### 12.2.3. Write/Read setting code for each mode.

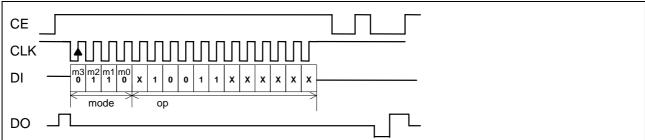
Mode	RTC
Write	0 h
Read	8 h

<sup>\*</sup> Please do not set any mode setting code other than the ones in the table above.

#### 12.3. Read / Write EEPROM Memory

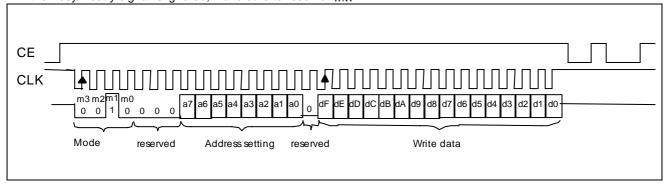
#### 12.3.1. Write Enable mode (EWEN)

- 1) After power supply, please execute this once.
- 2) If data has been transferred while Busy, the Write Enable mode may be canceled. In this case, execute again the Write Enable mode.



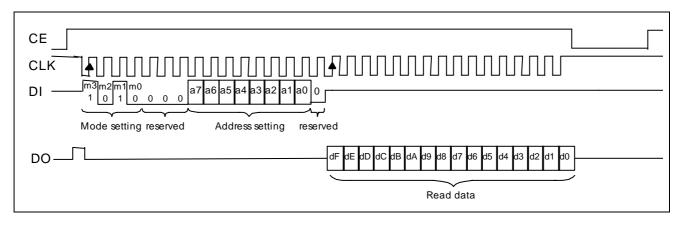
#### 12.3.2. Write EEPROM Memory

- 1) At power supply, set the Write Enable mode (Write Enable mode section [12.3.1.]).
- 2) After CE input rises, set the mode into the mode field (4 bits), and then make sure to set the segment bits (3 bits) of the address field to 0 because these are used for memory expansion. Set the address into the next 8 bits, and then set the following bit to "0". Finally, write the data in the data field.
- \* If the Busy/Ready signal is ignored, make sure to reserve two.

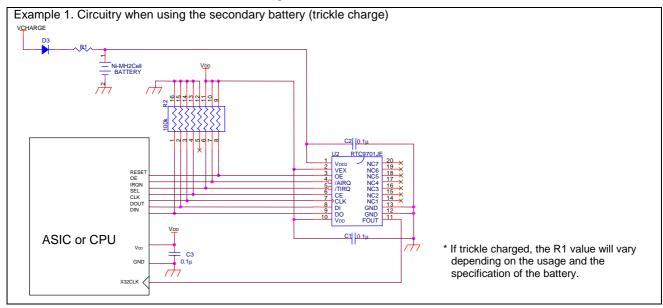


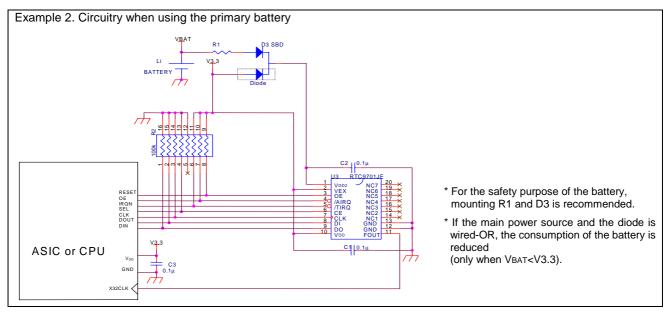
#### 12.3.3. Read EEPROM Memory

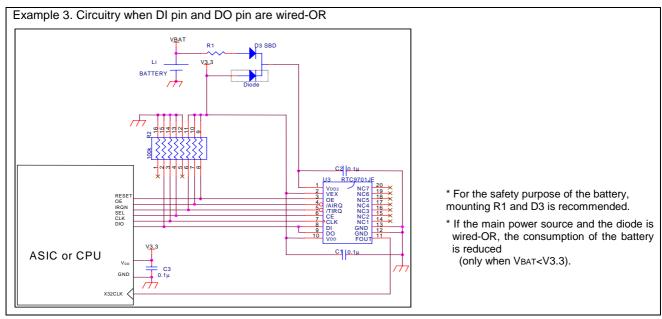
- 1) After setting the address, data can be transferred. This mode can be used only when the EEPROM Memory mode is set.
- 2) After CE input rises, set the mode into the mode field (4 bits), and then make sure to set the segment bits (3 bits) of the address field to 0 because these are used for memory expansion. Set the address into the next 8 bits, and then set the following bit to "0". The next 16 bits data is output from DO.
- \* If the Busy/Ready signal is ignored, make sure to reserve 16 ms once every second.



## 13. External connection examples

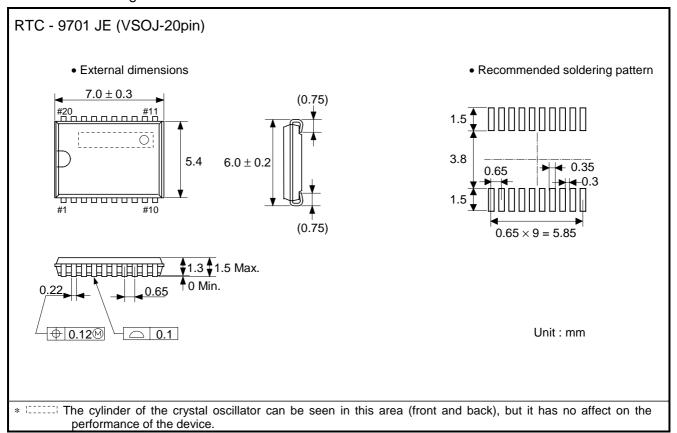




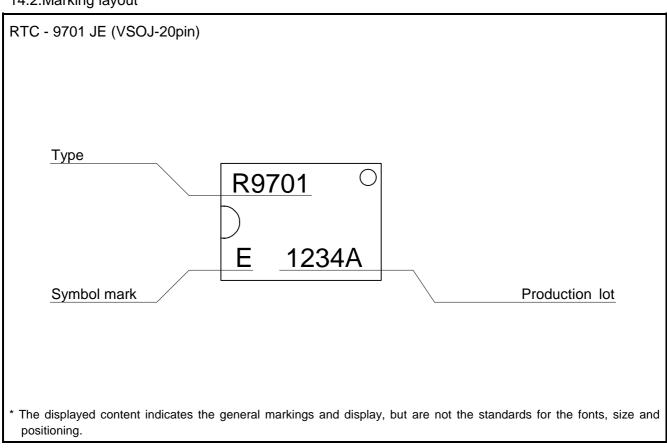


## 14. External diagram / Marking layout

## 14.1. External diagram

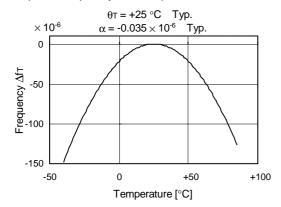


#### 14.2.Marking layout

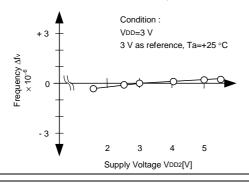


## 15. Reference data

(1) Example of frequency and temperature characteristics



(2) Example of frequency and voltage characteristics



[Finding the frequency stability]

1. Frequency and temperature characteristics can be approximated using the following equations.

$$\Delta \mathsf{f} \mathsf{T} = \alpha \left( \theta \mathsf{T} - \theta \mathsf{X} \right)^2$$

 $\Delta fT$ : Frequency deviation in any

temperature

(1 / °C<sup>2</sup>) : Coefficient of secondary temperature

 $(-0.035\pm0.005)\times10^{-6}\,\text{/°C}^2$ 

 $\theta T$  (°C) : Ultimate temperature (+25±5 °C)

 $\theta x$  (°C) : Any temperature

2. To determine overall clock accuracy, add the frequency precision and voltage characteristics.

$$\Delta f/f = \Delta f/fo + \Delta fT + \Delta fV$$

 $\Delta f/f$ : Clock accuracy (stable frequency) in any

temperature and voltage

 $\Delta f/fo$ : Frequency precision

 $\Delta f_T$  : Frequency deviation in any temperature

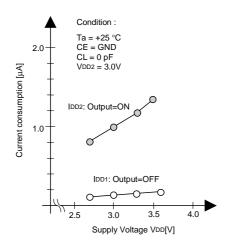
Δfv : Frequency deviation in any voltage

3. How to find the date difference Date difference =  $\Delta f/f \times 86400$  (seconds)

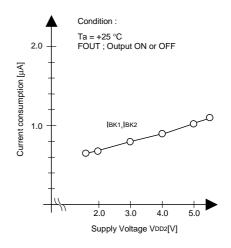
\* For example:  $\Delta f/f = 11.574 \times 10^{-6}$  is an error of approximately 1 second/day.

(3) Current and voltage consumption characteristics

(3-1) VDD Current consumption (IDD1, IDD2)



(3-2) VDD2 Current consumption (IBK1, IBK2)



## 16. Application notes

#### 16.1. Notes on handling

This module uses a C-MOS IC to realize low power consumption. Carefully note the following cautions when handling. (1) Static electricity

While this module has built-in circuitry designed to protect it against electrostatic discharge, the chip could still be damaged by a large discharge of static electricity. Containers used for packing and transport should be constructed of conductive materials. In addition, only soldering irons, measurement circuits, and other such devices which do not leak high voltage should be used with this module, which should also be grounded when such devices are being used.

#### (2) Noise

If a signal with excessive external noise is applied to the power supply or input pins, the device may malfunction or "latch up." In order to ensure stable operation, connect a filter capacitor (preferably ceramic) of greater that 0.1  $\mu$ F as close as possible to the power supply pins ( between VDD and GND, between VDD2 and GND, and between VEX and GND). Also, avoid placing any device that generates high level of electronic noise near this module.

\* Do not connect signal lines to the shaded area in the figure shown in Fig.1 and, if possible, embed this area in a GND land.

#### (3) Voltage levels of input pins

When the input pins are at the mid-level, this will cause increased current consumption and a reduced noise margin, and can impair the functioning of the device. Therefore, try as much as possible to apply the voltage level close to VDD or GND.

#### (4) Handling of unused pins

Since the input impedance of the input pins is extremely high, operating the device with these pins in the open circuit state can lead to unstable voltage level and malfunctions due to noise. Therefore, pull-up or pull-down resistors should be provided for all unused input pins.

#### 16.2. Notes on packaging

#### (1) Soldering temperature conditions

If the temperature within the package exceeds +260 °C, the characteristics of the crystal oscillator will be degraded and it may be damaged. Therefore, always check the mounting temperature before mounting this device. Also, check again if the mounting conditions are later changed.

\* See Fig.2 for the soldering conditions.

#### (2) Mounting equipment

While this module can be used with general-purpose mounting equipment, the internal crystal oscillator may be damaged in some circumstances, depending on the equipment and conditions. Therefore, be sure to check this. In addition, if the mounting conditions are later changed, the same check should be performed again.

#### (3) Ultrasonic cleaning

Depending on the usage conditions, there is a possibility that the crystal oscillator will be damaged by resonance during ultrasonic cleaning. Since the conditions under which ultrasonic cleaning is carried out (the type of cleaner, power level, time, state of the inside of the cleaning vessel, etc.) vary widely, this device is not warranted against damage during ultrasonic cleaning.

#### (4) Mounting orientation

This device can be damaged if it is mounted in the wrong orientation. Always confirm the orientation of the device before mounting.

#### (5) Leakage between pins

Leakage between pins may occur if the power is turned on while the device has condensation or dirt on it. Make sure the device is dry and clean before supplying power to it.

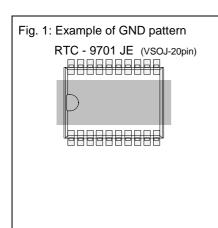


Fig. 2 : Fig. 2 : Reference profile for our evaluation of Soldering heat resistance. Temperature [°C]  $\frac{+240 \text{ °C Max.}}{+235 \text{ °C} \pm 5 \text{ °C}}$   $\frac{+240 \text{ °C Max.}}{+235 \text{ °C} \pm 10 \text{ °C}}$   $\frac{+150 \text{ °C} \pm 10 \text{ °C}}{+300 \text{ °C}}$ 

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Time [s]

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